

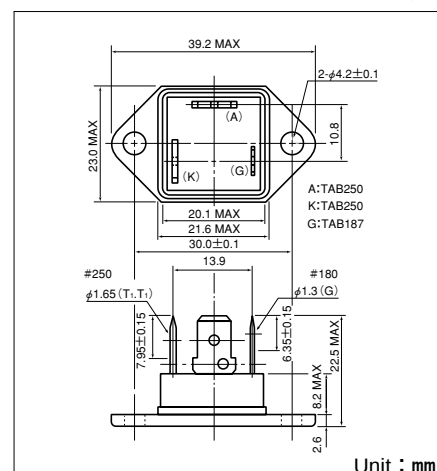
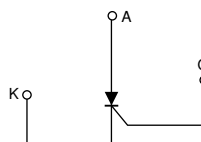
THYRISTOR MODULE (ISOLATED MOLD TYPE)

SG25AA

UL:E76102 (M)

SG25AA is an isolated molded thyristor which is suitable for a wide range of industrial and home electronics uses. SG25AA uses highly reliable glass passivation.

- $I_{T(AV)}=25A$
- high Surge Capability
- Tab terminals for easy wiring.



Maximum Ratings

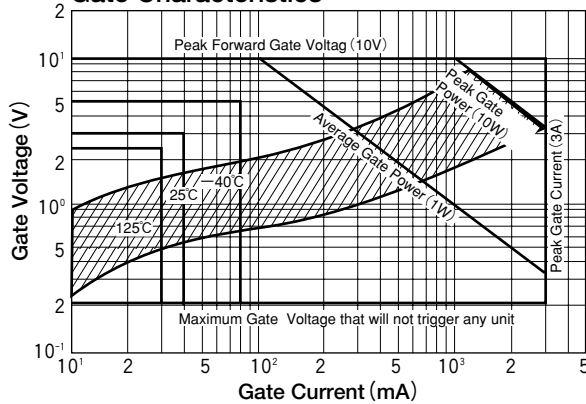
Symbol	Item	Ratings			Unit
		SG25AA20	SG25AA40	SG25AA60	
VRRM	Repetitive Peak Reverse Voltage	200	400	600	V
VRSM	Non-Repetitive Peak Reverse Voltage	240	480	720	V
VDRM	Repetitive Peak Off-State Voltage	200	400	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(AV)}$	Average On-State Current	Single phase, half wave, 180° conduction, $T_c : 70^\circ C$	25	A
$I_{T(RMS)}$	R.M.S. On-State Current	Single phase, half wave, 180° conduction, $T_c : 70^\circ C$	39	A
I_{TSM}	Surge On-State Current	$\frac{1}{2}$ cycle, 50Hz/60Hz, peak value, non-repetitive	450/500	A
I^2t	I^2t	2~10ms	1040	A ² S
P _{GM}	Peak Gate Power Dissipation		10	W
P _{G(AV)}	Average Gate Power Dissipation		1	W
I _{FGM}	Peak Gate Current		3	A
V _{FGM}	Peak Gate Voltage(Forward)		10	V
V _{RGM}	Peak Gate Voltage(Reverse)		5	V
di/dt	Critical Rate of Rise of On-State Current	$I_G=100mA$, $T_j=25^\circ C$, $V_D=\frac{1}{2}V_{DRM}$, $dI_G/dt=1A/\mu s$	100	A/ μs
V _{ISO}	Isolation Breakdown Voltage (R.M.S.)	A.C.1minute	2500	V
T _j	Operating Junction Temperature		-40 to +125	°C
T _{stg}	Storage Temperature		-40 to +125	°C
	Mounting Torque (M4)	Recommended Value 1.0-1.4 (10-14)	1.5 (15)	N·m (kgf·cm)
	Mass		23	g

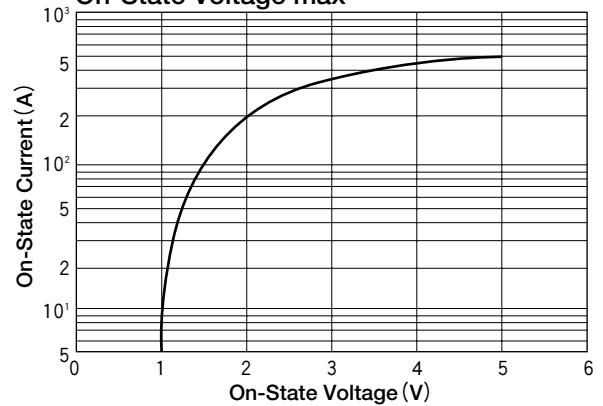
Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I _{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM} , single phase, half wave, $T_j=125^\circ C$	5	mA
I _{RRM}	Repetitive Peak Reverse Current, max.	at V_{DRM} , single phase, half wave, $T_j=125^\circ C$	5	mA
V _{TM}	Peak On-State Voltage, max.	On-State Current 78A, $T_j=25^\circ C$ Inst. measurement	1.40	V
I _{GT} /V _{GT}	Gate Trigger Current/Voltage, max.	$T_j=25^\circ C$, $I_T=1A$, $V_D=6V$	40/3	mA/V
V _{GD}	Non-Trigger Gate, Voltage. min.	$T_j=125^\circ C$, $V_D=\frac{1}{2}V_{DRM}$	0.2	V
t _{gt}	Turn On Time, max.	$I_T=25A$, $I_G=100mA$, $T_j=25^\circ C$, $V_D=\frac{1}{2}V_{DRM}$, $dI_G/dt=1A/\mu s$	10	μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_j=125^\circ C$, $V_D=\frac{2}{3}V_{DRM}$, Exponential wave.	100	V/ μs
I _H	Holding Current, typ.	$T_j=25^\circ C$	30	mA
R _{th(j-c)}	Thermal Impedance, max.	Junction to case	1.6	°C/W

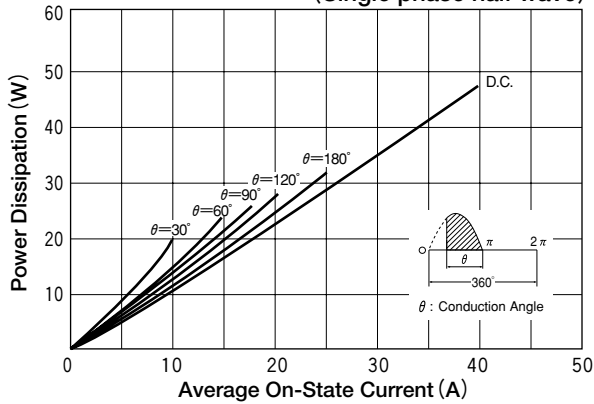
Gate Characteristics



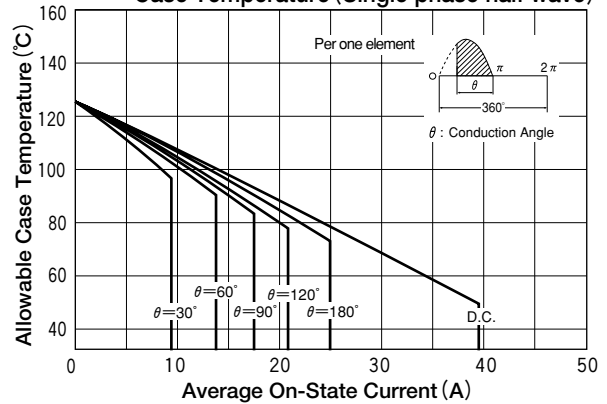
On-State Voltage max



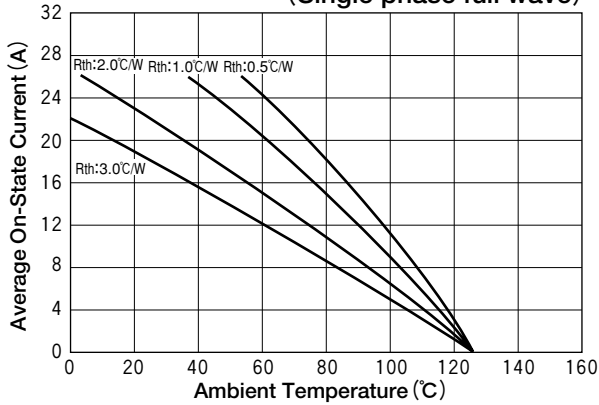
Average On-State Current Vs Power Dissipation (Single phase half wave)



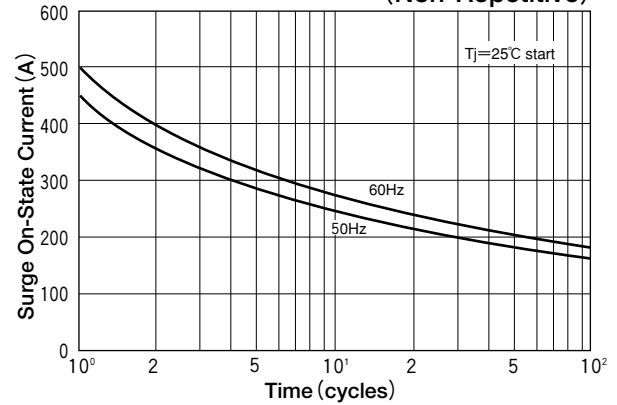
Average On-State Current Vs Maximum Allowable Case Temperature (Single phase half wave)



Ambient Temperature Average On-State (Single phase full wave)



Surge On-State Current Rating (Non-Repetitive)



Transient Thermal Impedance

